

isc Silicon NPN Power Transistor

BUV89

DESCRIPTION

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 800V(\text{Min})$
- High Switching Speed

APPLICATIONS

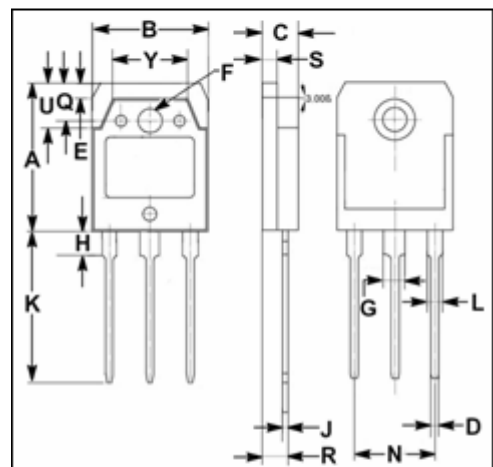
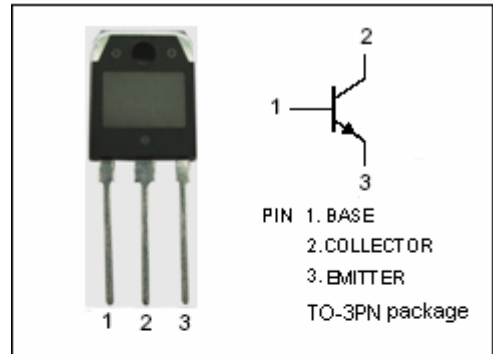
- Designed for use in AC motor control systems from three-phase mains.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector- Emitter Voltage $V_{BE}=0$	1200	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	8	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current-Continuous	4	A
$I_{BM}$	Base Current-Peak	6	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	125	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

## isc Silicon NPN Power Transistor

## BUV89

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.1\text{A}; I_B=0; L=25\text{mH}$	800			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=4.5\text{A}; I_B=2\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=3\text{A}$		1.0		V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4.5\text{A}; I_B=2\text{A}$			1.3	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=V_{CESmax}; V_{BE}=0$ $V_{CE}=V_{CESmax}; V_{BE}=0; T_J=125^\circ\text{C}$			1 2	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	mA
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	8			
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		125		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=5\text{V}; f_{test}=5\text{MHz}$		7		MHz

## Switching Times; Resistive Load

$t_{on}$	Turn-On Time	$I_C=4.5\text{A}; I_{B1}=-I_{B2}=2\text{A}$		0.2		$\mu\text{s}$
$t_s$	Storage Time			3.5		$\mu\text{s}$
$t_f$	Fall Time			0.5		$\mu\text{s}$